

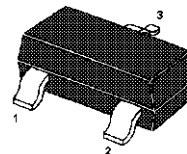
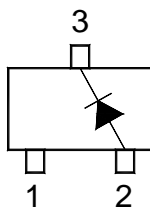
1SS196

SILICON EPITAXIAL PLANAR DIODE

SOT-23

Features

- Small package
- Low forward voltage
- Fast reverse recovery time
- Small total capacitance



Marking Code: FD

SOT-23 Plastic Package

Applications

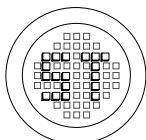
Ultra high speed switching application

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	V_{RM}	85	V
Reverse Voltage	V_R	80	V
Maximum Peak Forward Current	I_{FM}	300	mA
Surge Current (10ms)	I_{FSM}	2	A
Average Forward Current	I_O	100	mA
Power Dissipation	P_{tot}	150	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_s	-55 to +150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min	Max	Unit
Forward Voltage at $I_F = 100\text{mA}$	V_F	-	1.2	V
Reverse Current at $V_R = 80\text{V}$	I_R	-	0.5	μA
Total Capacitance at $V_R = 0, f = 1\text{MHz}$	C_T	-	3	pF
Reverse Recovery Time at $I_F = 10\text{mA}$	t_{rr}	-	4	ns



®

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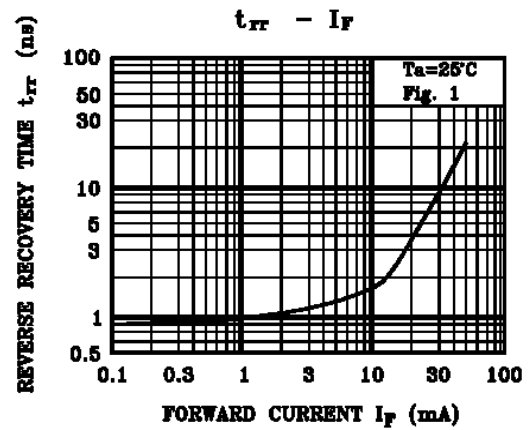
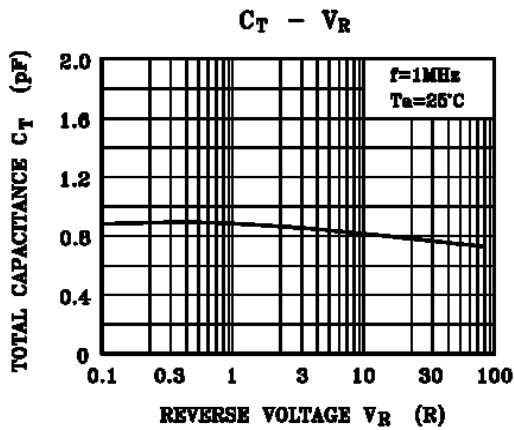
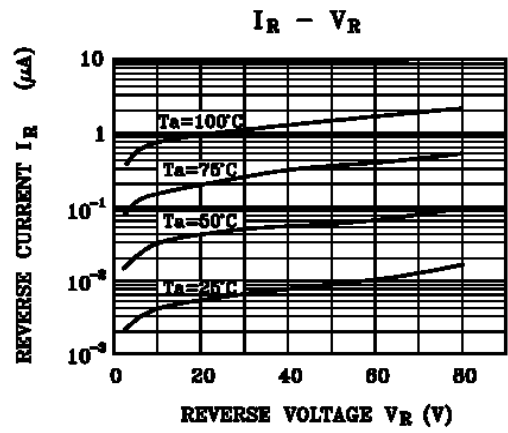
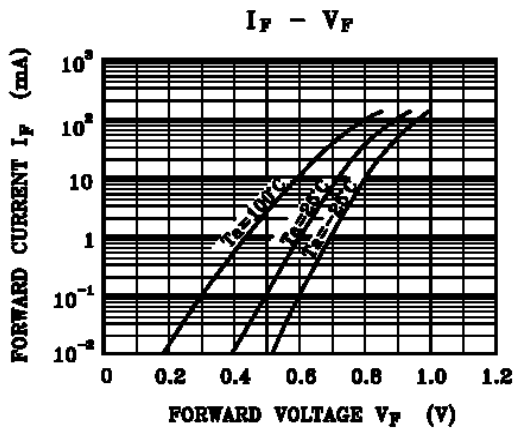
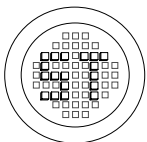
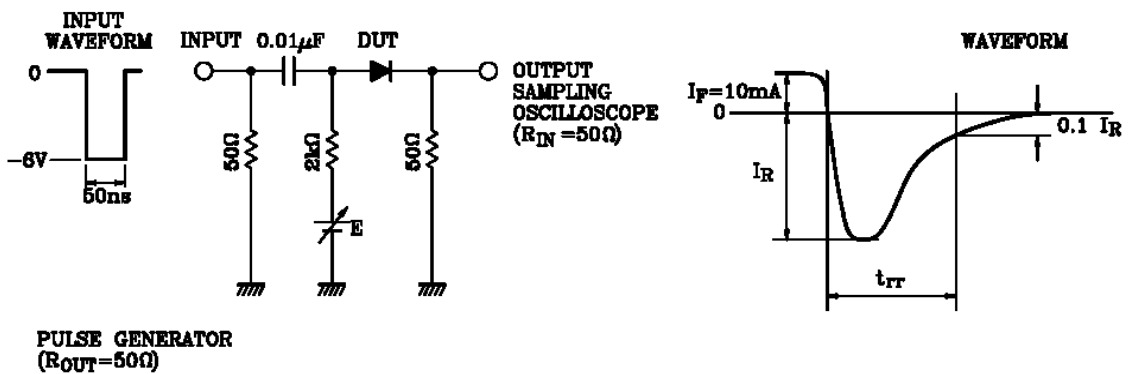


Fig. 1. REVERSE RECOVERY TIME(t_{rr}) TEST CIRCUIT



SEMTECH ELECTRONICS LTD.

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